

L Number	Hits	Search Text	DB	Time stamp
1	1258464	polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:08
2	470779	(silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:20
3	80200	(polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:10
4	236569	(semiconductor silicon si gaas) with wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:10
5	15173	((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:10
6	14402	(substrate carrier) and ((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:11
7	13824	((integrated adj circuit) ic device chip die dice) and ((substrate carrier) and ((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with wafer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:11
8	1510	dicing and ((substrate carrier) and ((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with wafer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:22
9	1493	dicing and (((integrated adj circuit) ic device chip die dice) and ((substrate carrier) and ((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with wafer))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:14

10	365661	(critical strain) with (strain energy release rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 14:37
11	213	(dicing and (((integrated adj circuit) ic device chip die dice) and ((substrate carrier) and ((polyester phenolic polyimide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with wafer)))) and ((critical strain) with (strain energy release rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:16
12	410378	(silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:21
13	213	(polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((dicing and (((integrated adj circuit) ic device chip die dice) and ((substrate carrier) and ((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with wafer)))) and ((critical strain) with (strain energy release rate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:21
14	14580	(polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:21
15	35388	(critical) with (strain energy release rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:33
16	309	((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)) and ((critical) with (strain energy release rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:21

17	16	dicing and (((polyester phenolic polyimide polyimide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)) and ((critical) with (strain energy release rate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:22
18	55208	(critical strain) with (energy release rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:33
19	461	((polyester phenolic polyimide polyimide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)) and ((critical strain) with (energy release rate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:33
20	44	((polyester phenolic polyimide polyimide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)) and ((critical strain) with (energy release rate))) and (dicing diced dice)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:34
21	30	((polyester phenolic polyimide polyimide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)) and ((critical strain) with (energy release rate))) and (dicing diced dice)) not (dicing and (((polyester phenolic polyimide polyimide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)) and ((critical) with (strain energy release rate))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:46
22	2061	257/780	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:46
23	848	257/790	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:46
24	1221	257/788	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:46

25	621	257/789	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:46
26	2228	257/790 257/788 257/789	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:46
27	280	(257/790 257/788 257/789) and (polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:47
28	110	((257/790 257/788 257/789) and (polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terephthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 14:35
29	1372	polyarylene adj ether	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 14:36
30	428	((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg) and (polyarylene adj ether)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 14:37
31	19	((critical strain) with (strain energy release rate)) and (((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg) and (polyarylene adj ether)).	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 14:37